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Edward M. Cantrell

For: SEMICONDUCTOR DEVICE
AND METHOD FOR FORMING
THE SAME

March 7, 2001

In response to the Examiner's non-final Office Action mailed September 7, 2000, the period for responding having been extended Three (3) months, please consider the following amendments and remarks in connection with the above-identified application.

Please amend claim 15 as follows:

15. (Amended) A CMOS semiconductor device having an N-channel type thin film transistor and a P-channel type thin film transistor, each of which comprising:
- a first insulating film comprising silicon nitride formed on a substrate;
 - a second insulating film comprising silicon oxide formed on said first insulating film;
 - a semiconductor layer formed on said second insulating film wherein said semiconductor layer includes at least source, drain and channel regions;
 - a third insulating film comprising silicon oxide formed on said semiconductor layer;